

## IR2103STRPBF-HX Half-Bridge Driver

### Description

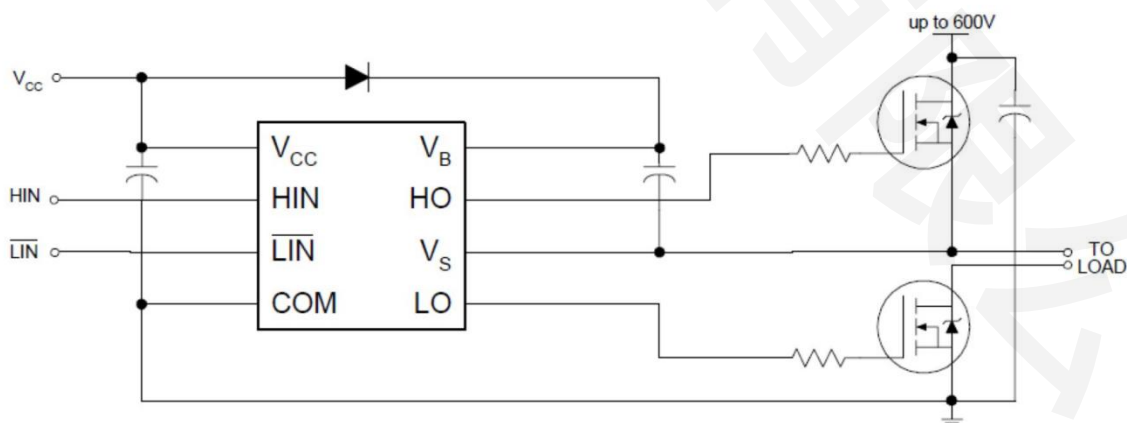
The IR2103STRPBF-HX is a high-voltage, high-speed driver designed for power MOSFETs and IGBTs, featuring dependent output channels referenced to both the high and low sides. Utilizing proprietary HVIC and latch-immune CMOS technologies, this device offers robust monolithic construction. The logic input is compatible with standard CMOS or LSTTL outputs down to 3.3V logic levels.

The output drivers are equipped with a high pulse current buffer stage specifically engineered to minimize cross-conduction between drivers. The floating channel can effectively drive an N-channel power MOSFET or IGBT in a high-side configuration, operating at voltages of up to 600 volts.

### Features

- ★ Floating channel designed for bootstrap operation
- ★ Fully operational to +600V
- ★ Tolerant to negative transient voltage
- ★ dV/dt immune
- ★ Gate drive supply range from 10 to 20V
- ★ Undervoltage lockout
- ★ 3.3V, 5V and 15V logic compatible
- ★ Cross-conduction prevention logic
- ★ Matched propagation delay for both channels
- ★ Internal set deadtime
- ★ High side output in phase with HIN input
- ★ Low side output out of phase with LIN input

### Connection Diagram



(Refer to Lead Assignments for correct configuration). This/These diagram(s) show electrical connections only. Please refer to our Application Notes and Design Tips for proper circuit board layout.

## Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min	Max	Units	
V <sub>B</sub>	High side floating absolute voltage	-0.3	625	V	
V <sub>S</sub>	High side floating supply offset voltage	V <sub>B</sub> - 25	V <sub>B</sub> + 0.3		
V <sub>HO</sub>	High side floating output voltage	V <sub>S</sub> - 0.3	V <sub>B</sub> + 0.3		
V <sub>CC</sub>	Low side and logic fixed supply voltage	-0.3	25		
V <sub>LO</sub>	Low side output voltage	-0.3	V <sub>CC</sub> + 0.3		
V <sub>IN</sub>	Logic input voltage (HIN & $\overline{\text{LIN}}$ )	-0.3	V <sub>CC</sub> + 0.3		
dV <sub>S</sub> /dt	Allowable offset supply voltage transient	—	50	V/ns	
PD	Package power dissipation @ T <sub>A</sub> ≤ +25. °C	8 lead SOIC	—	0.625	W
R <sub>thJA</sub>	Thermal resistance, junction to ambient	8 lead SOIC	—	200	°C/W
T <sub>J</sub>	Junction temperature	—	150	°C	
T <sub>S</sub>	Storage temperature	-55	150		
T <sub>L</sub>	Lead temperature (soldering, 10 seconds)	—	300		

## Recommended Operating Conditions

The input/output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The V<sub>S</sub> offset rating is tested with all supplies biased at 15V differential.

Symbol	Definition	Min	Max	Units
V <sub>B</sub>	High side floating absolute voltage	V <sub>S</sub> + 10	V <sub>S</sub> + 20	V
V <sub>S</sub>	High side floating supply offset voltage	†	600	
V <sub>HO</sub>	High side floating output voltage	V <sub>S</sub>	V <sub>B</sub>	
V <sub>CC</sub>	Low side and logic fixed supply voltage	10	20	
V <sub>LO</sub>	Low side output voltage	0	V <sub>CC</sub>	
V <sub>IN</sub>	Logic input voltage (HIN & $\overline{\text{LIN}}$ )	0	V <sub>CC</sub>	
T <sub>A</sub>	Ambient temperature	-40	125	°C

Logic operational for V<sub>S</sub> of -5 to +600V. Logic state held for V<sub>S</sub> of -5V to -V<sub>BS</sub>. (Please refer to the Design Tip DT97-3 for more details).

## Dynamic Electrical Characteristics

VBIAS (VCC, VBS) = 15V, CL = 1000 pF and TA = 25°C unless otherwise specified.

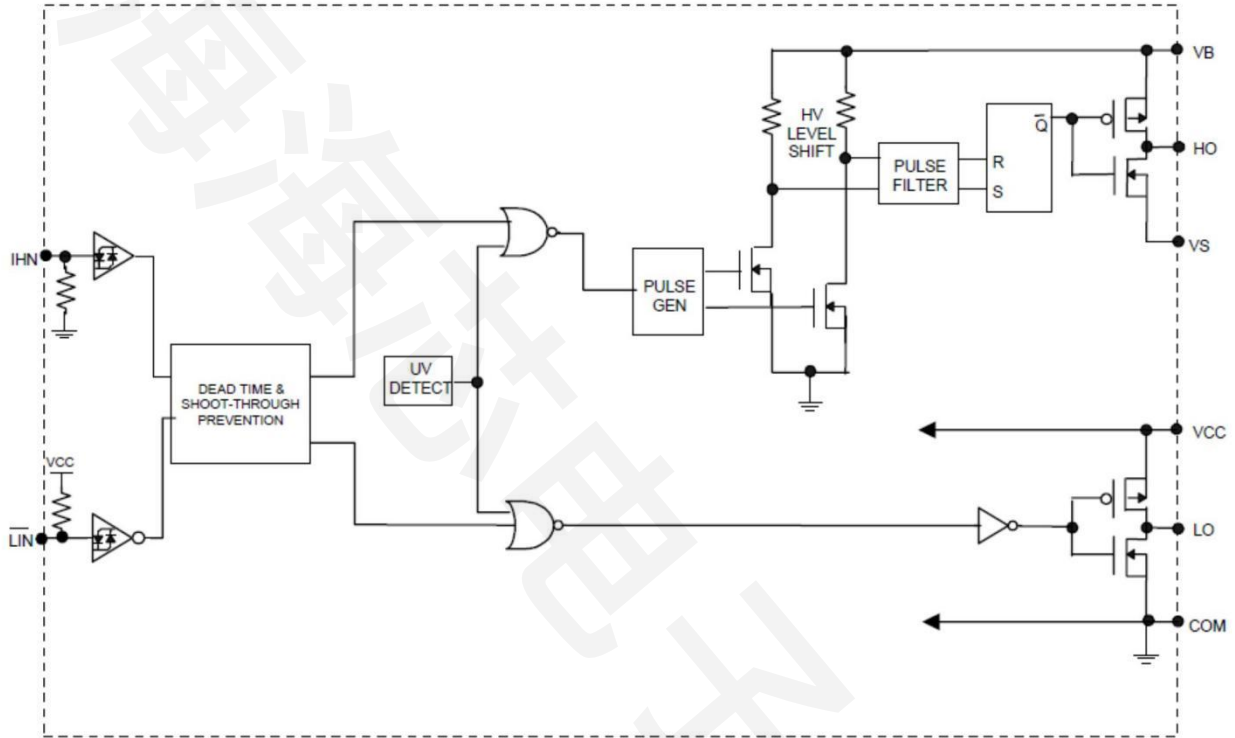
Symbol	Definition	Min	Typ	Max	Units	Test Conditions
ton	Turn-on propagation delay	—	680	820	ns	VS = 0V
toff	Turn-off propagation delay	—	150	220		VS = 600V
tr	Turn-on rise time	—	100	170		
tf	Turn-off fall time	—	50	60		
DT	Deadtime, LS turn-off to HS turn-on & HS turn-on to LS turn-off	400	520	650		
MT	Delay matching, HS & LS turn on/off	—	—	60		

## Static Electrical Characteristics

VBIAS (VCC, VBS) = 15V and TA = 25°C unless otherwise specified. The VIN, VTH, and IIN parameters are referenced to COM. The VO and IO parameters are referenced to COM and are applicable to the respective output leads: HO or LO.

Symbol	Definition	Min	Typ	Max	Units	Test Conditions
VIH	Logic —1  (HIN) & Logic —0  (L $\bar{N}$ ) input voltage	3	—	—	V	VCC = 10V to 20V
VIL	Logic —0  (HIN) & Logic —1  (L $\bar{N}$ ) input voltage	—	—	0.8		VCC = 10V to 20V
VOH	High level output voltage VBIAS - VO	—	—	100	mV	IO = 0A
VOL	Low level output voltage, VO	—	—	100		IO = 0A
ILK	Offset supply leakage current	—	—	50	μA	VB = VS = 600V
IQBS	Quiescent VBS supply current	—	30	55		VIN = 0V or 5V
IQCC	Quiescent VCC supply current	—	150	270		VIN = 0V or 5V
IIN+	Logic —1  input bias current	—	3	10		HIN = 5V, L $\bar{N}$ = 0V
IIN-	Logic —0  input bias current	—	—	1	HIN = 0V, LIN = 5V	
VCCUV+	VCC supply undervoltage positive going threshold	8	8.9	9.8	V	
VCCUV-	VCC supply undervoltage negative going threshold	7.4	8.2	9		
IO+	Output high short circuit pulsed current	130	210	—	mA	VO = 0V, VIN = VIH PW ≤ 10 μs
IO-	Output low short circuit pulsed current	270	360	—		VO = 15V, VIN = VIL PW ≤ 10 μs

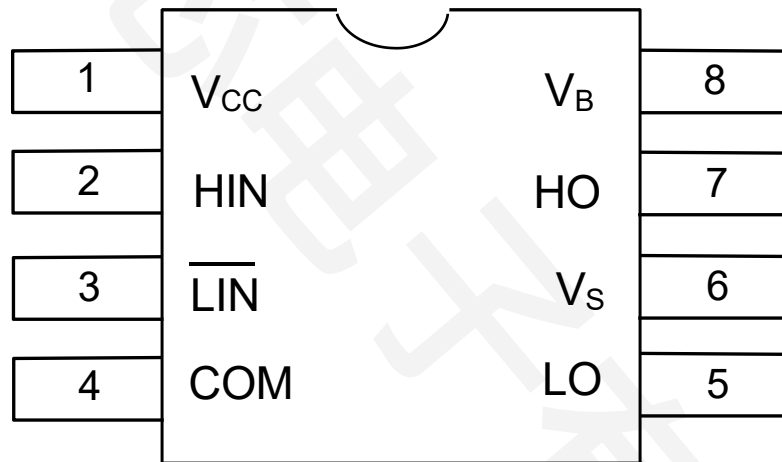
## Functional Block Diagram



## Lead Definitions

Symbol	Description
HIN	Logic input for high side gate driver output (HO), in phase
$\overline{\text{LIN}}$	Logic input for low side gate driver output (LO), out of phase
VB	High side floating supply
HO	High side gate drive output
Vs	High side floating supply return
Vcc	Low side and logic fixed supply
LO	Low side gate drive output
COM	Low side return

## Lead Assignments



## Application Information and Additional Details

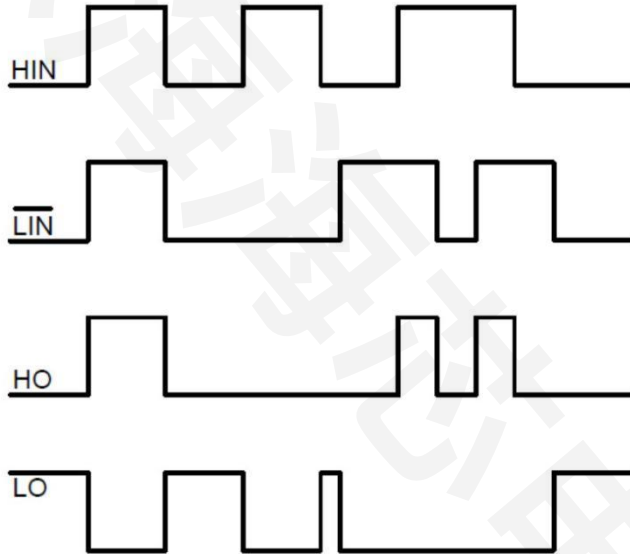


Figure 1. Input/Output Timing Diagram

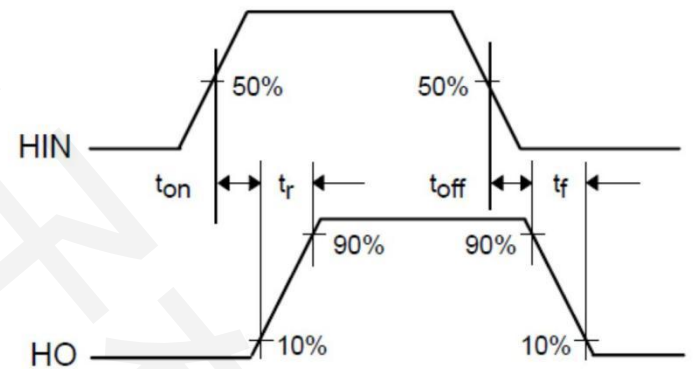
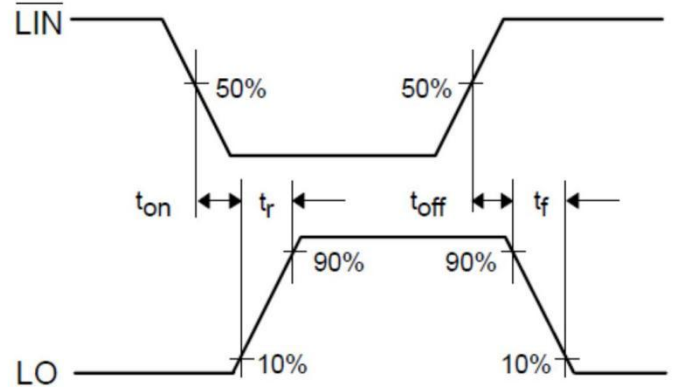


Figure 2. Switching Time Waveform Definitions

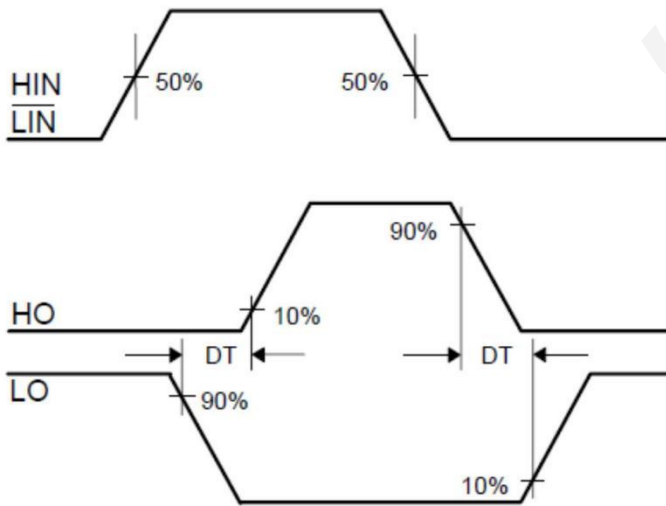


Figure 3. Deadtime Waveform Definitions

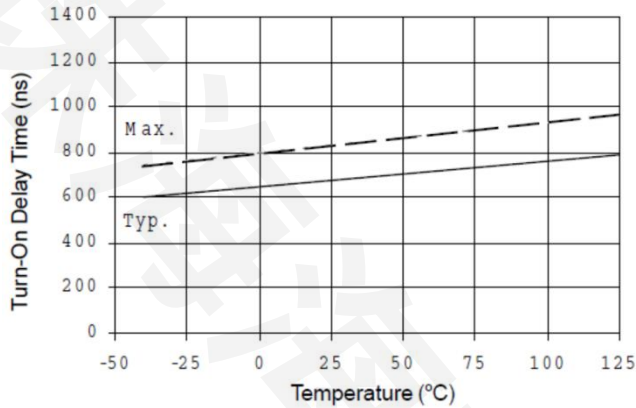


Figure 4A. Turn-On Time vs. Temperature

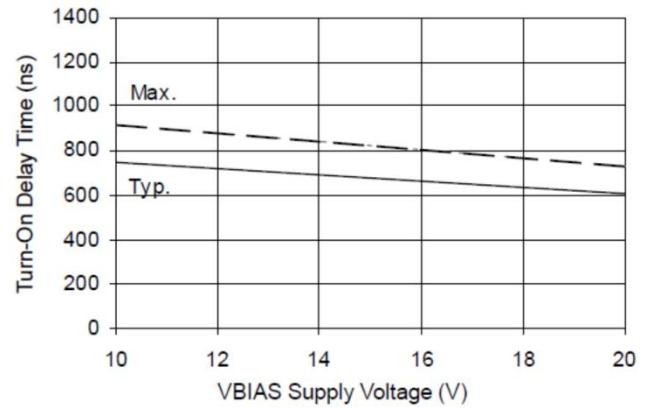


Figure 4B. Turn-On Time vs. Supply Voltage

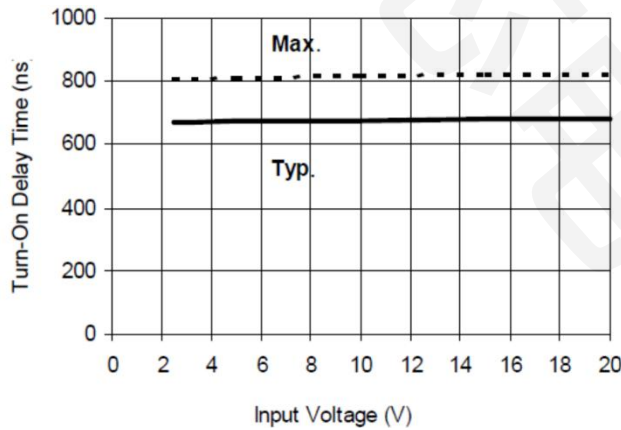


Figure 4C. Turn-On Time vs. Input Voltage

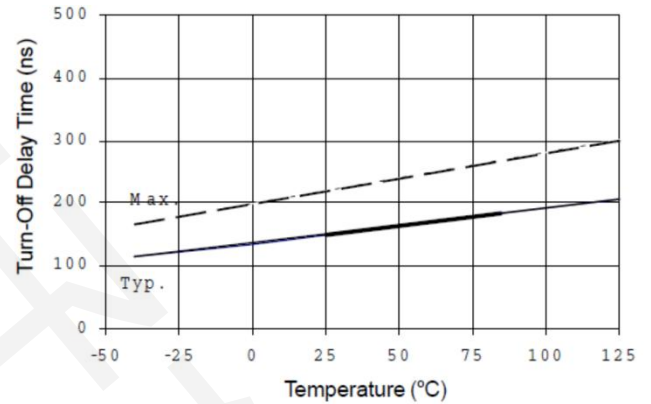


Figure 5A. Turn-Off Time vs. Temperature

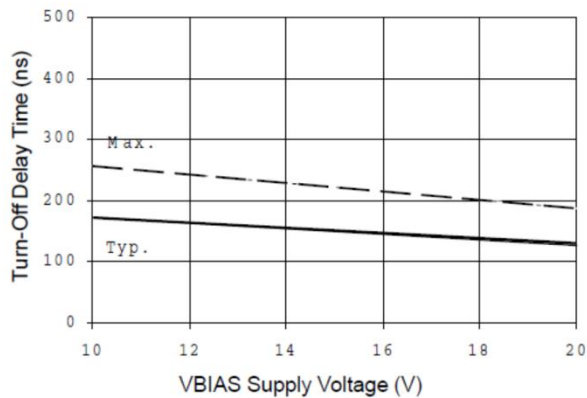


Figure 5B. Turn-Off Time vs. Supply Voltage

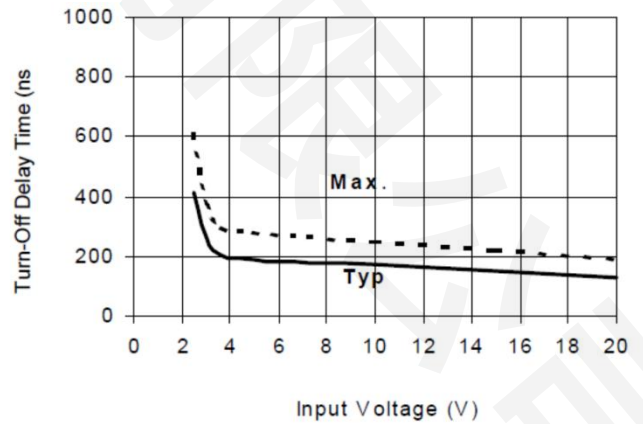


Figure 5C. Turn-Off Time vs. Input Voltage

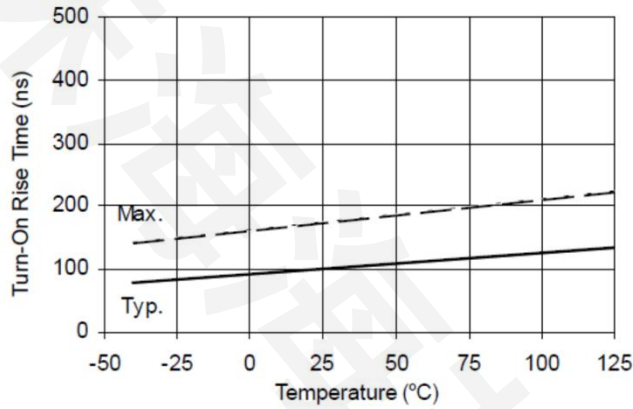


Figure 6A. Turn-On Rise Time vs. Temperature

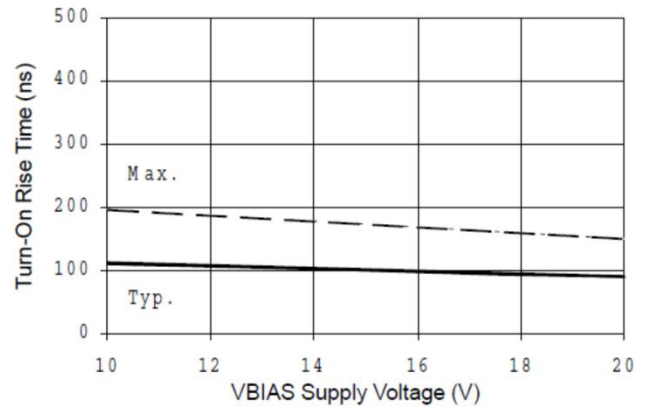


Figure 6B. Turn-On Rise Time vs. Voltage

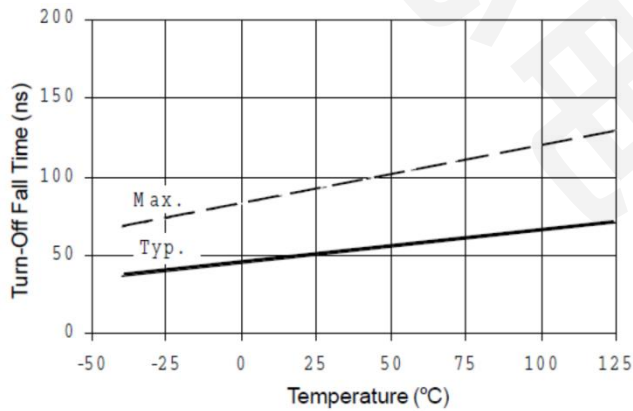


Figure 7A. Turn Off Fall Time vs. Temperature

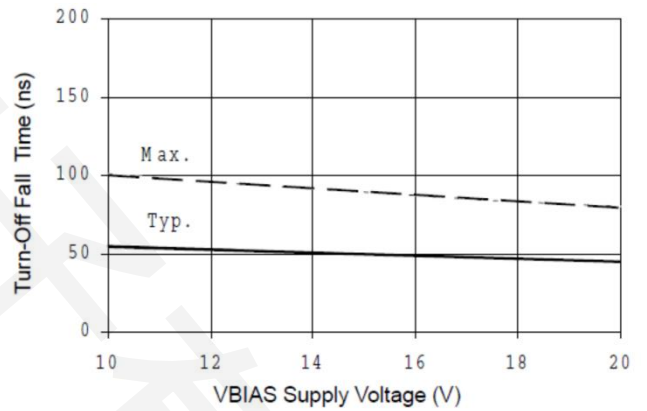


Figure 7B. Turn Off Fall Time vs. Voltage

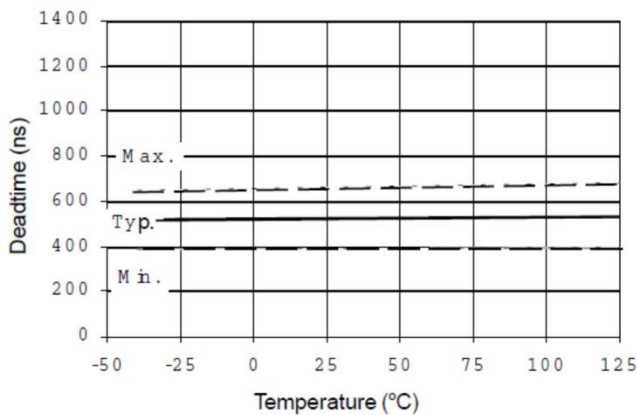


Figure 8A. Deadtime vs. Temperature

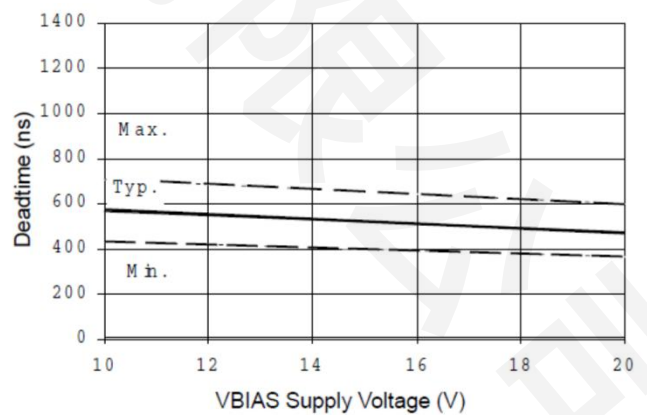


Figure 8B. Deadtime vs. Voltage

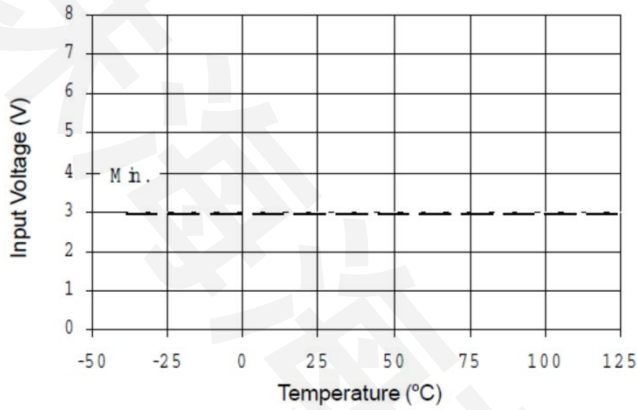


Figure 9A. Logic “1” ( HIN) & Logic “0” ( LIN) Input Voltage vs. Temperature

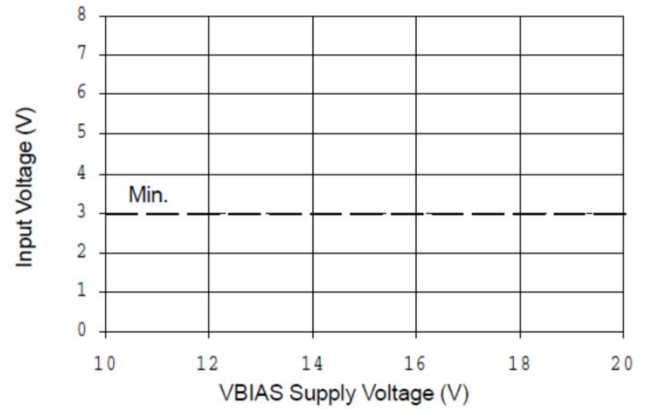


Figure 9B. Logic “1” ( HIN) & Logic “0” ( LIN) Voltage vs. Voltage

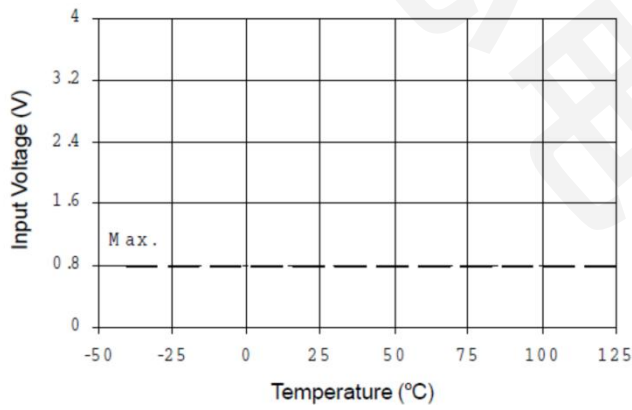


Figure 10A. Logic “0” ( HIN) & Logic “1” ( LIN) Input Voltage vs. Temperature

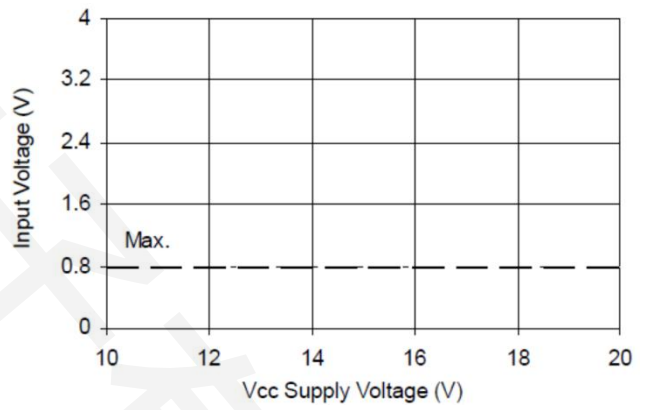


Figure 10B. Logic “0” ( HIN) & Logic “1” ( LIN) Voltage vs. Voltage

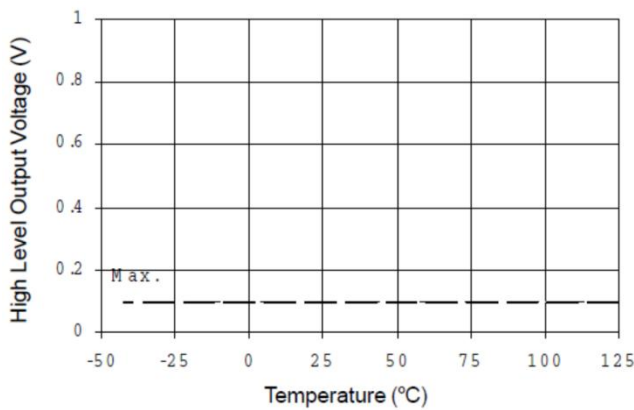


Figure 11A. High Level Output vs. Temperature

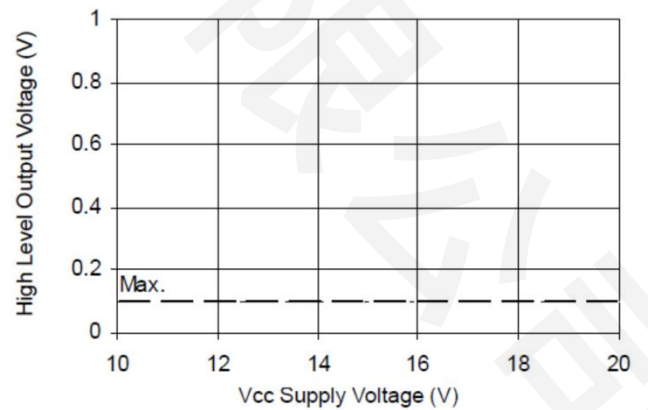


Figure 11B. High Level Output vs. Voltage

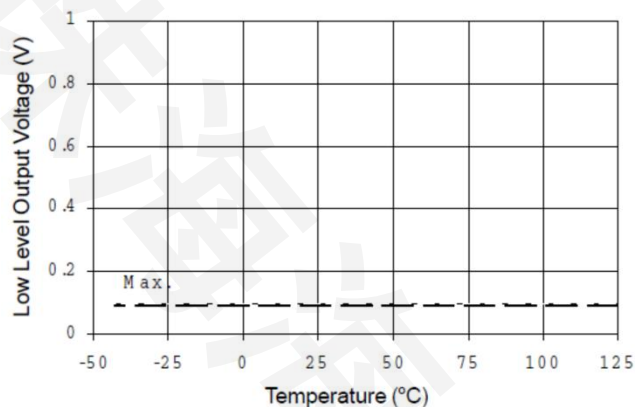


Figure 12A. Low Level Output vs. Temperature

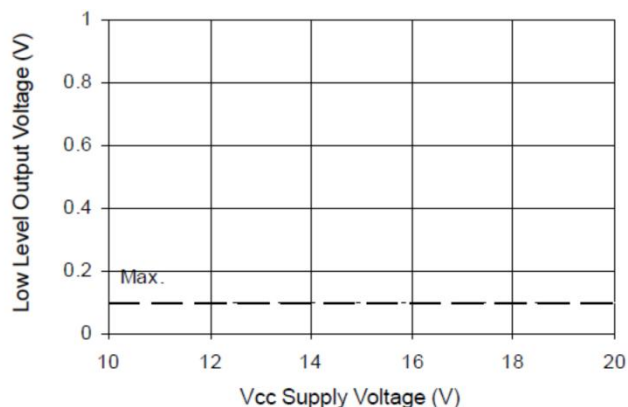


Figure 12B. Low Level Output vs. Voltage

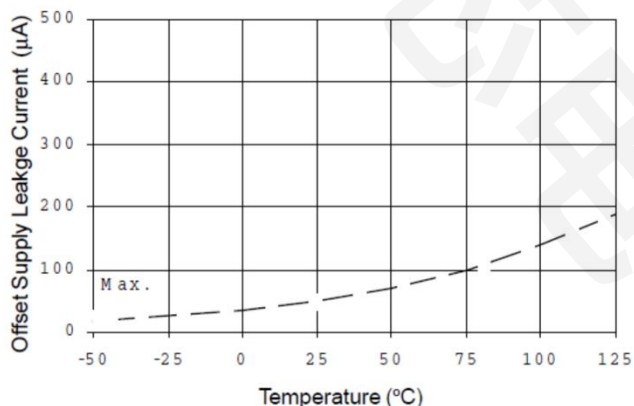


Figure 13A. Offset Supply Current vs. Temperature

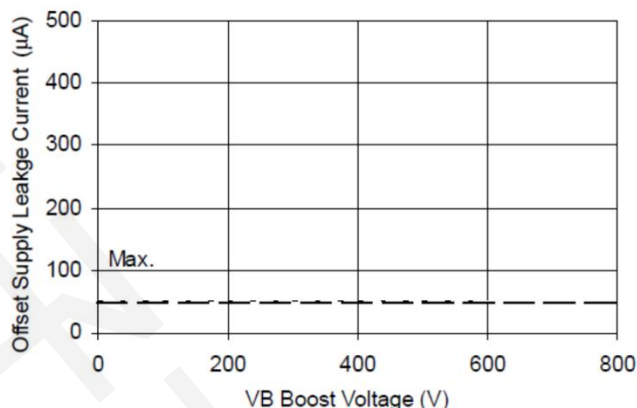


Figure 13B. Offset Supply Current vs. Voltage

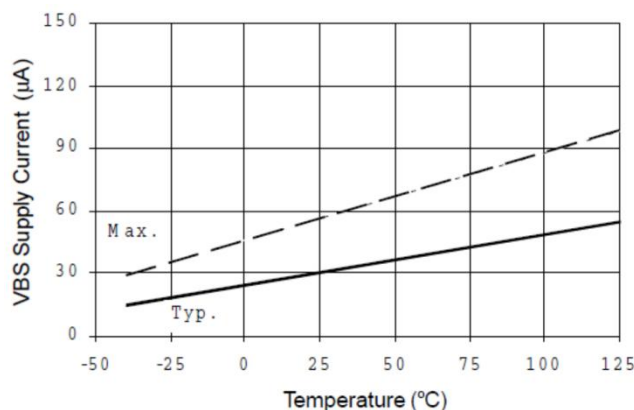


Figure 14A. VBS Supply Current vs. Temperature

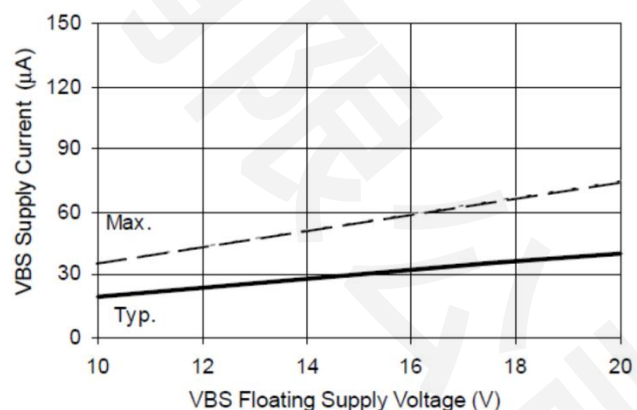


Figure 14B. VBS Supply Current vs. Voltage

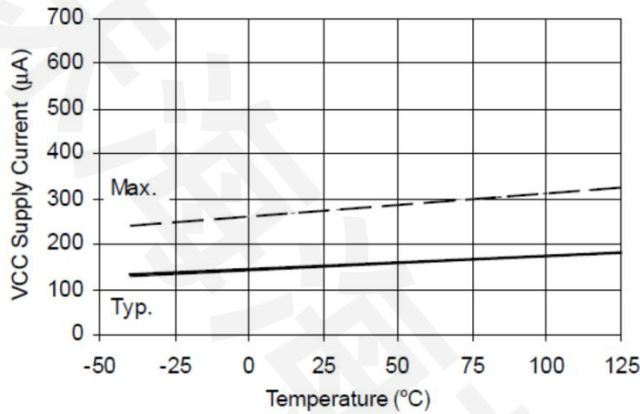


Figure 15A. VCC Supply Current vs. Temperature

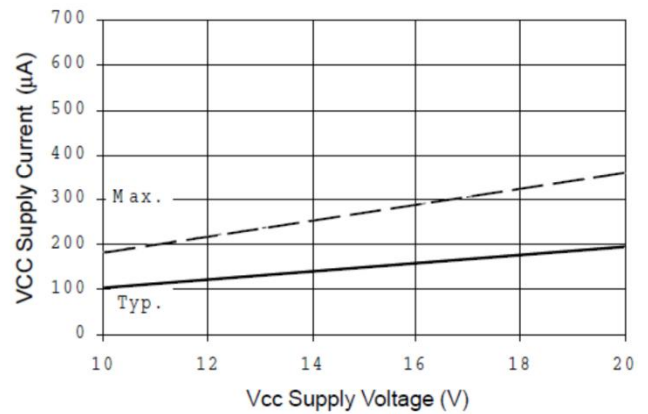


Figure 15B. VCC Supply Current vs. Voltage

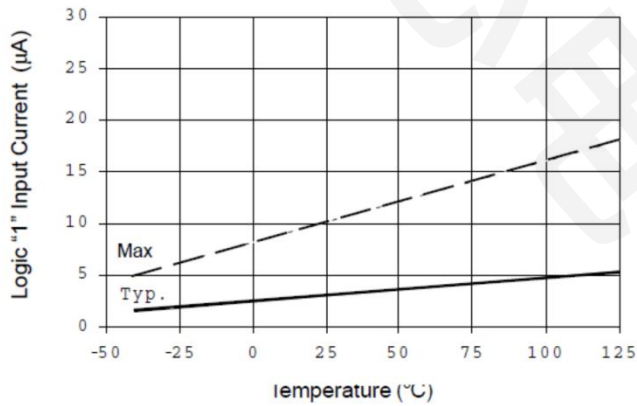


Figure 16A. Logic "1" Input Current vs. Temperature

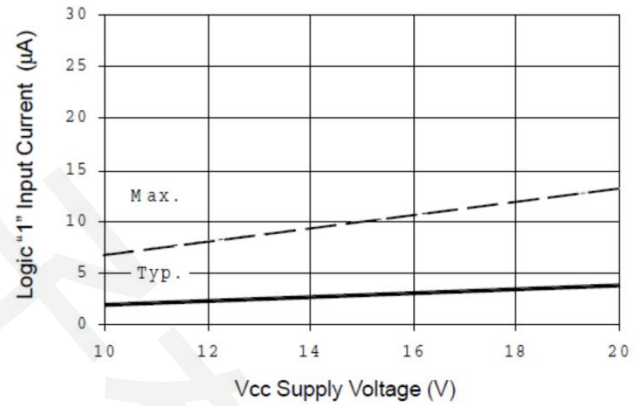


Figure 16B. Logic "1" Input Current vs. VCC Supply Voltage

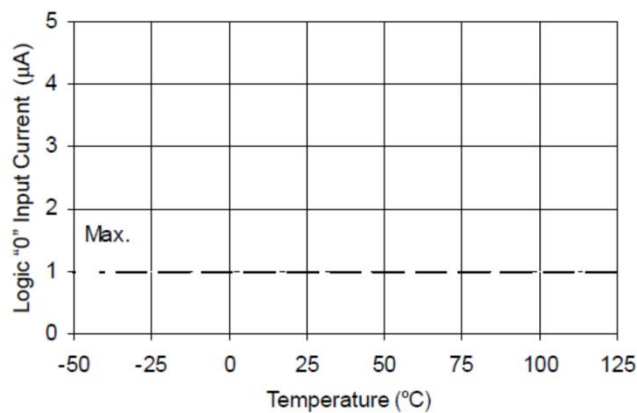


Figure 17A. Logic "0" Input Current vs. Temperature

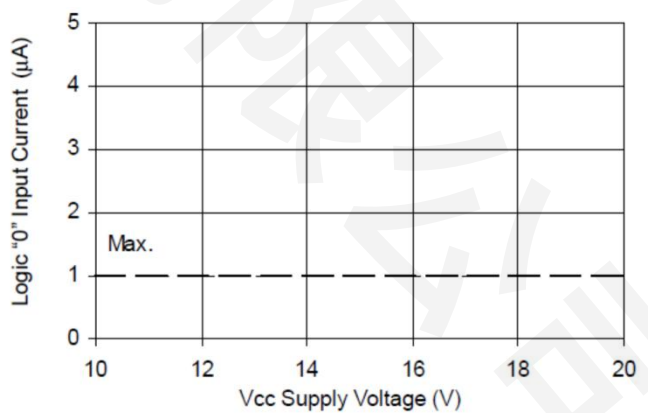


Figure 17B. Logic "0" Input Current vs. VCC Supply Voltage

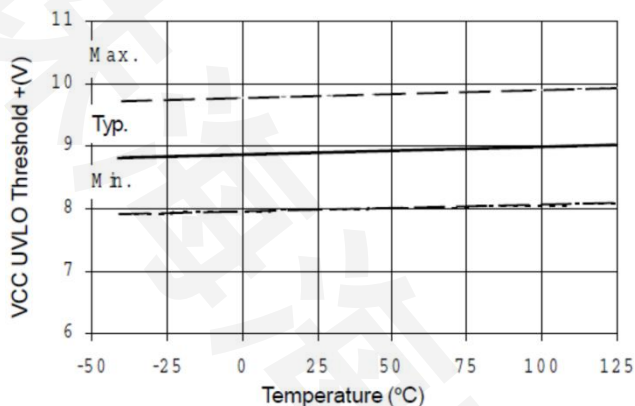


Figure 18A. VCC Undervoltage Threshold (+) vs. Temperature

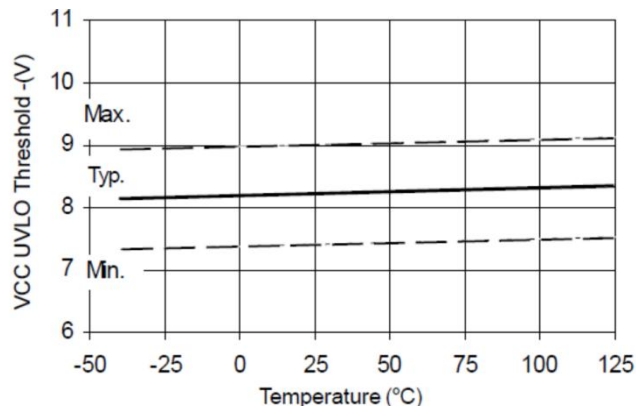


Figure 18B. VCC Undervoltage Threshold (-) vs. Temperature

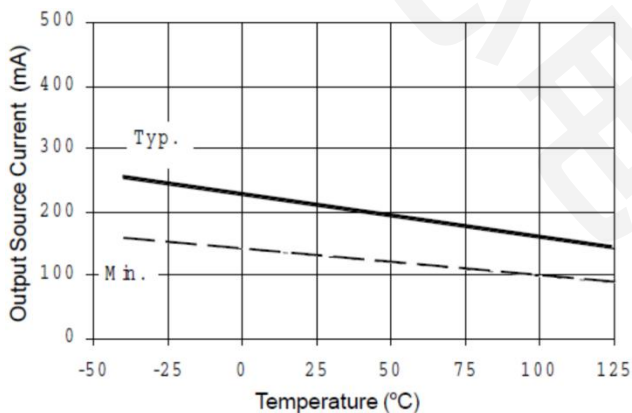


Figure 19A. Output Source Current vs. Temperature

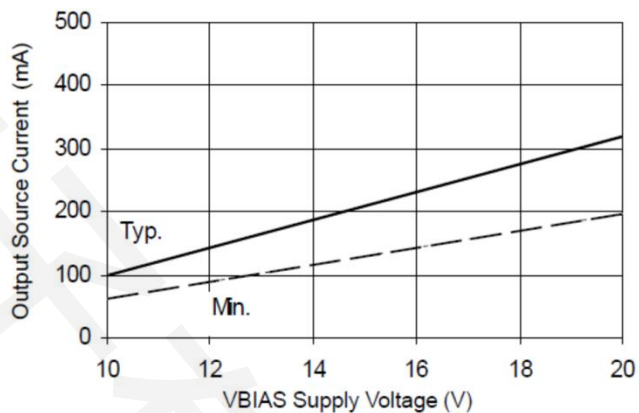


Figure 19B. Output Source Current vs. Voltage

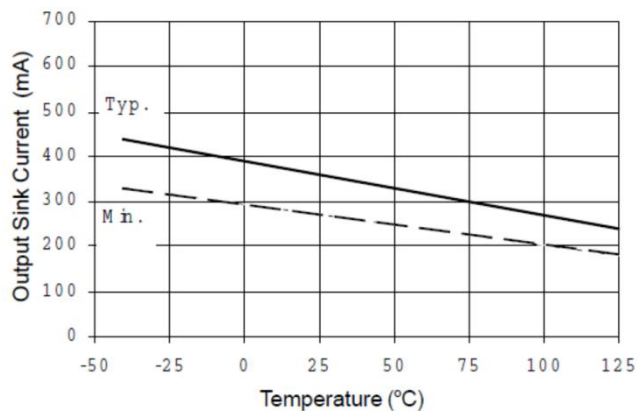


Figure 20A. Output Sink Current vs. Temperature

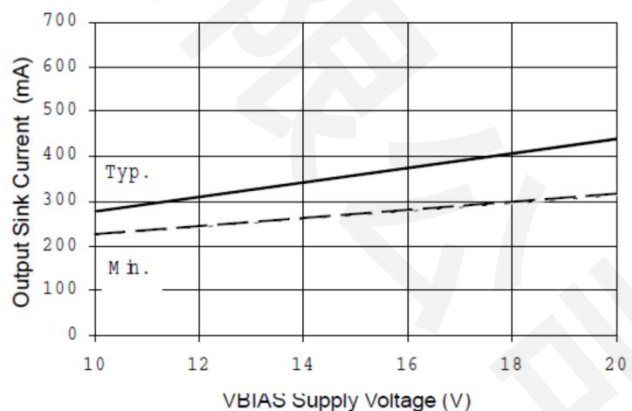
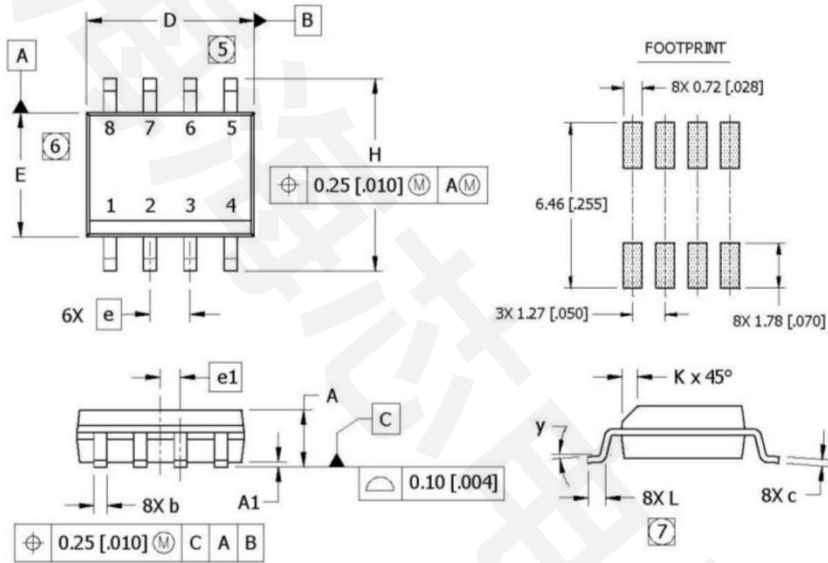


Figure 20B. Output Sink Current vs. Voltage

## Package Details

### SOIC-8



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

**NOTES:**

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.

5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.06].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.10].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.